

600V N-Channel MOSFET

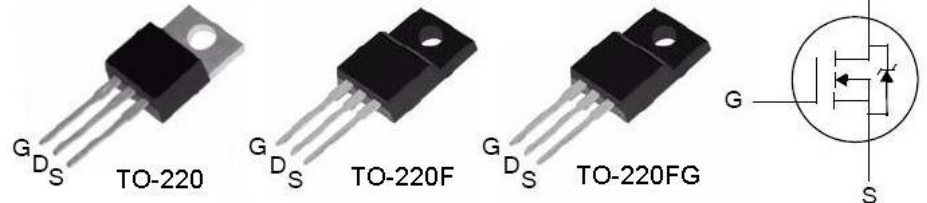
General Features

- Low ON Resistance
- Low Gate Charge (typical 54nC)
- Fast Switching
- 100% Avalanche Tested
- RoHS Compliant
- Halogen-free available

Applications

- High Efficiency SMPS
- Adaptor/Charger
- Active PFC
- LCD Panel Power

BV_{DSS}	$R_{DS(ON)}$ (Max.)	I_D
600V	0.75Ω	10.0A



Ordering Information

Part Number	Package	Marking	Remark
FTP10N60	TO-220	FTP10N60	RoHS
FTP10N60G	TO-220	FTP10N60G	Halogen-free
FTA10N60	TO-220F	FTA10N60	RoHS
FTA10N60G	TO-220F	FTA10N60G	Halogen-free
FTA10N60Z	TO-220FG	FTA10N60Z	RoHS
FTA10N60GZ	TO-220FG	FTA10N60GZ	Halogen-free

Absolute Maximum Ratings

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	FTP10N60	FTA10N60	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	600		V
I_D	Continuous Drain Current	10.0	10.0*	A
$I_D@100^\circ\text{C}$	Continuous Drain Current	Figure 3		
I_{DM}	Pulsed Drain Current, $V_{GS}@10V^{[2]}$	Figure 6		
P_D	Power Dissipation	156	50	W
	Derating Factor above 25°C	1.25	0.4	W/°C
V_{GS}	Gate-to-Source Voltage	±30		V
E_{AS}	Single Pulse Avalanche Energy $L=12\text{mH}$, $I_D=10\text{A}$	600		mJ
dv/dt	Peak Diode Recovery dv/dt ^[3]	4.5		V/ns
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300		°C
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150		

*Drain Current limited by Maximum Junction Temperature.

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	FTP10N60	FTA10N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.8	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	60	60	

Electrical Characteristics

OFF Characteristics

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	--	0.7	--	V/°C	Reference to 25°C, $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	20	μA	$V_{DS}=600V, V_{GS}=0V$
		--	--	100		$V_{DS}=480V, V_{GS}=0V,$ $T_C=125^\circ C$
I_{GSS}	Gate-to-Source Leakage Current	--	--	100	nA	$V_{GS}=+30V$
		--	--	-100		$V_{GS}=-30V$

ON Characteristics

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	0.65	0.75	Ω	$V_{GS}=10V, I_D=5.0A^{[4]}$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS} = V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance	--	10.3	--	S	$V_{DS} = 40V, I_D=10A^{[4]}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	1809	--	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$ Figure 14
C_{OSS}	Output Capacitance	--	142	--		
C_{RSS}	Reverse Transfer Capacitance	--	27.4	--		
Q_G	Total Gate Charge	--	54	--	nC	$V_{DD}=300V$ $I_D=10A$ Figure 15
Q_{GS}	Gate-to-Source Charge	--	7.7	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	25.3	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	44	--	ns	$V_{DD}=300V$ $I_D=10A$ $V_{GS}=10V$ $R_G=25\Omega$
t_{rise}	Rise Time	--	116	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	120	--		
t_{fall}	Fall Time	--	77	--		

Source-Drain Diode Characteristics
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
I_{SD}	Continuous Source Current (Body Diode)	--	--	10	A	Integral P-N diode in MOSFET
I_{SM}	Maximum Pulsed Current (Body Diode)	--	--	40	A	
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_S=10\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	--	337	--	ns	$V_{GS}=0\text{V}$ $I_F=10\text{A}$, $di/dt=100\text{A}/\mu\text{s}$
Q_{rr}	Reverse Recovery Charge	--	2.79	--	uC	

NOTE:

[1] $T_J=+25^{\circ}\text{C}$ to $+150^{\circ}\text{C}$

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] $I_{SD}=10\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J=+150^{\circ}\text{C}$

[4] Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

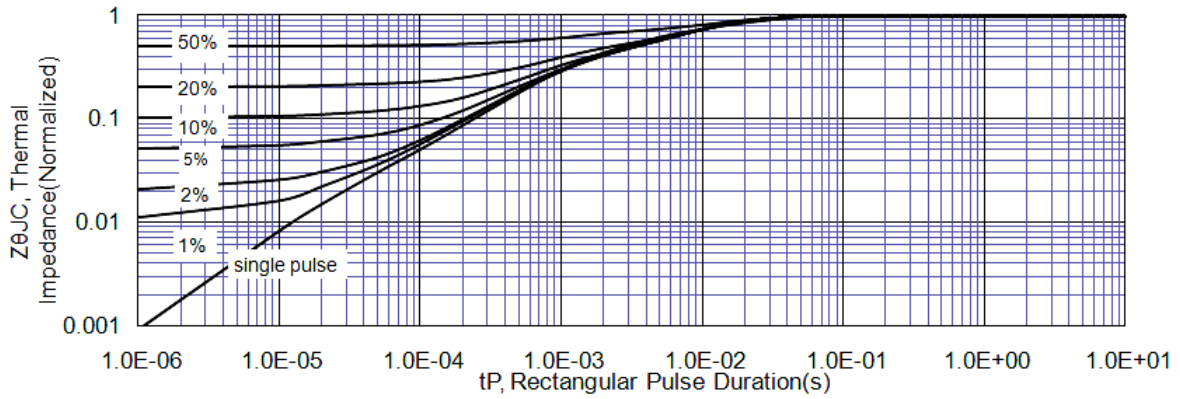
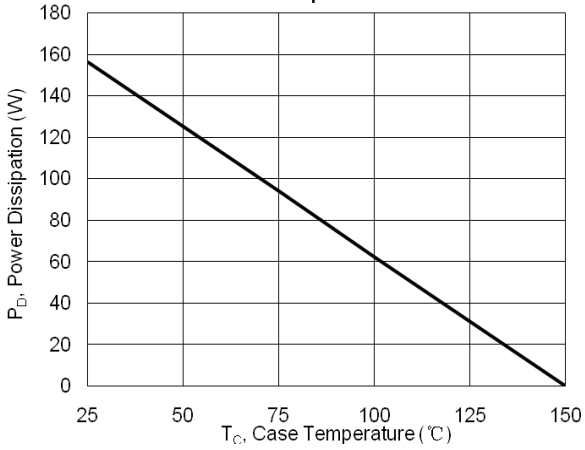
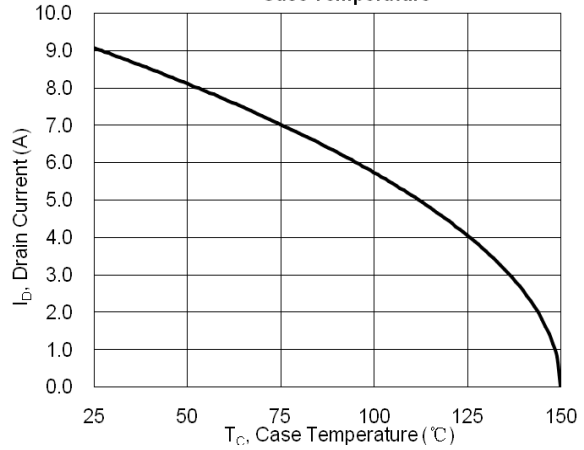
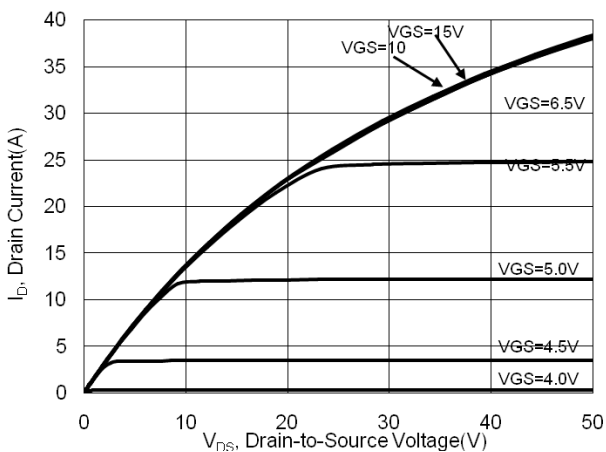
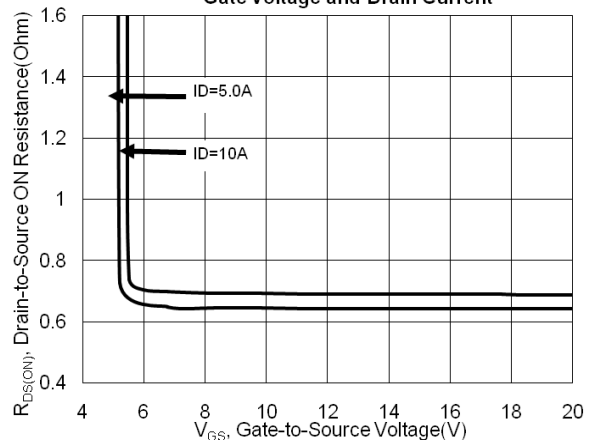
Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

Figure 2. Maximum Power Dissipation vs. Case Temperature

Figure 3. Maximum Continuous Drain Current vs Case Temperature

Figure 4. Typical Output Characteristics

Figure 5. Typical Drain-to-Source ON Resistance vs. Gate Voltage and Drain Current


Figure 6. Maximum Peak Current Capability

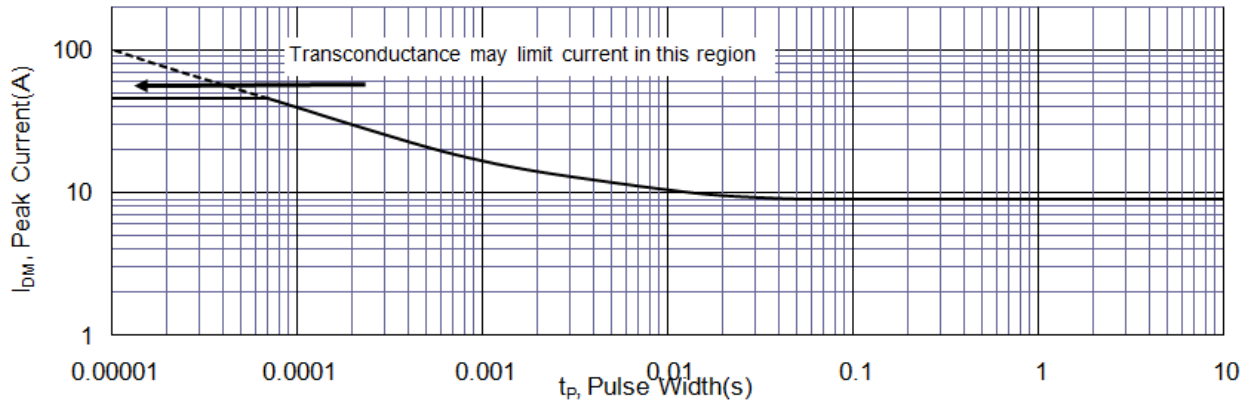


Figure 7. Typical Transfer Characteristics

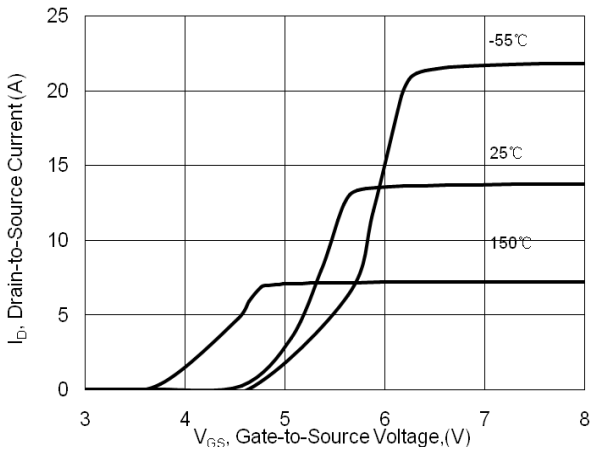


Figure 8. Unclamped Inductive Switching Capability

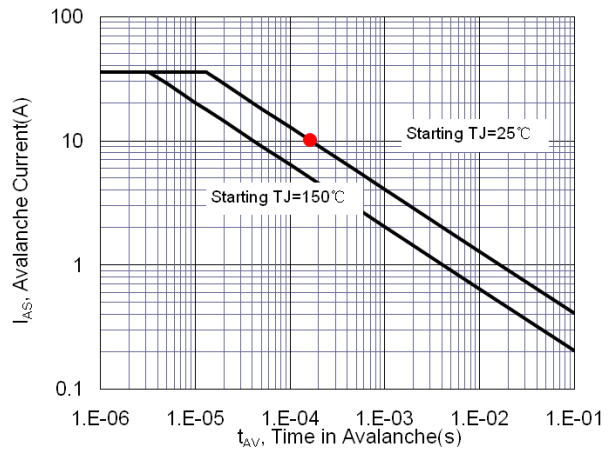


Figure 9. Typical Drain-to-Source ON Resistance

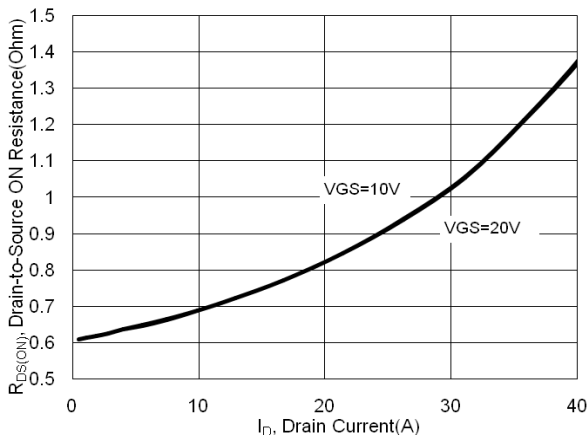


Figure 10. Typical Drain-to-Source On Resistance vs. Junction Temperature

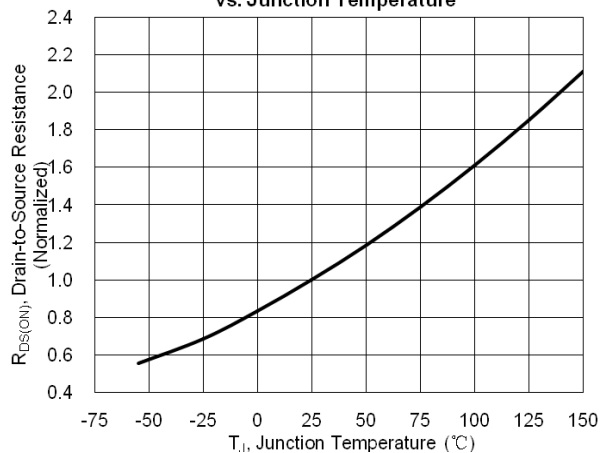


Figure 11. Typical Breakdown Voltage vs. Junction Temperature

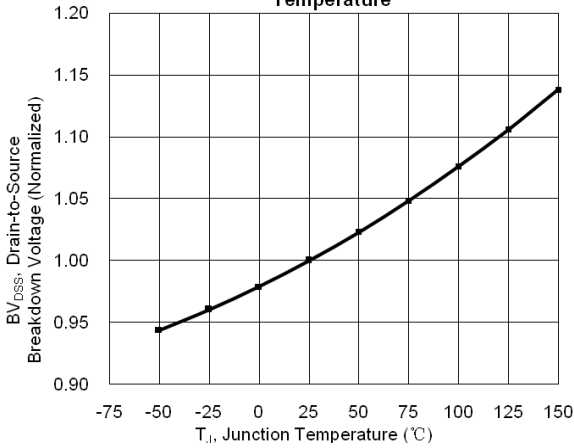


Figure 12. Typical Threshold Voltage vs. Junction Temperature

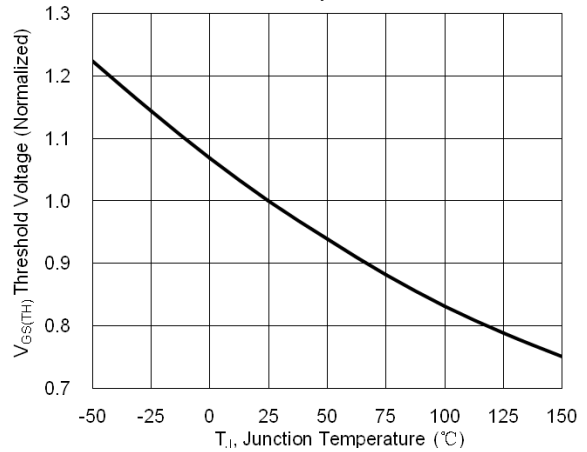


Figure 13. Maximum Forward Safe Operation Area

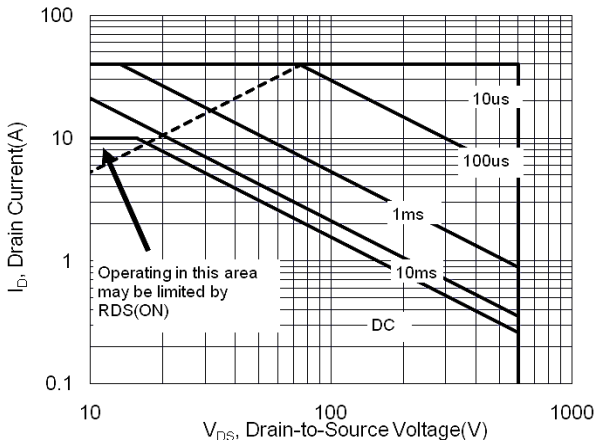


Figure 14. Typical Capacitance vs. Drain-to-Source Voltage

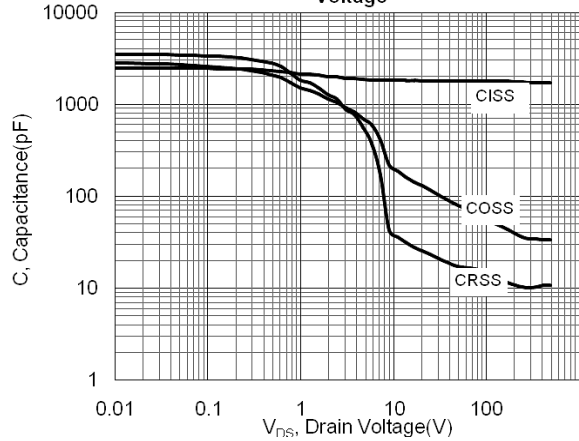


Figure 15. Typical Gate Charge vs. Gate-to-Source Voltage

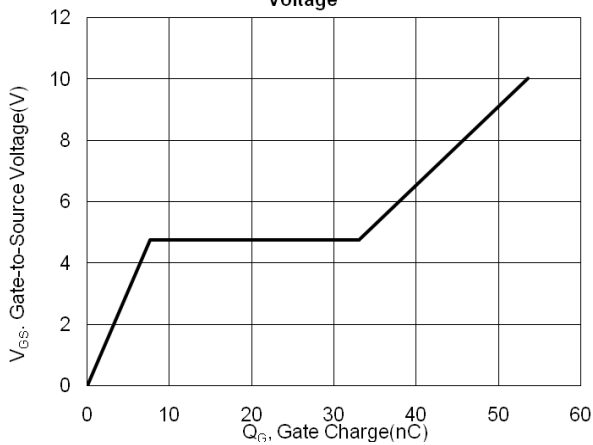
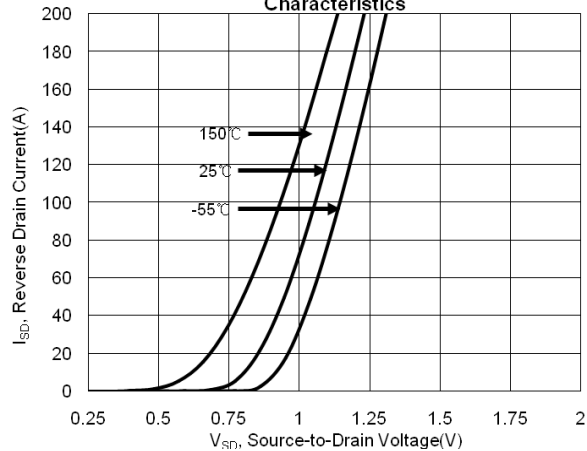
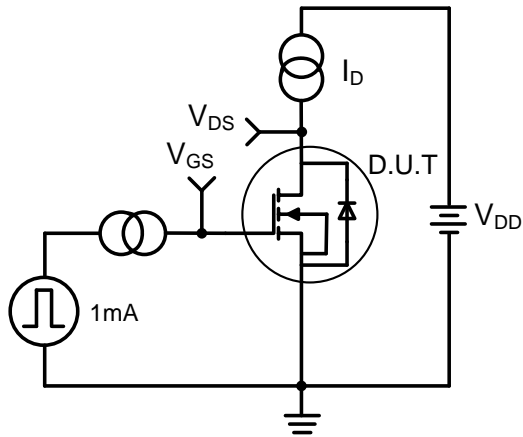
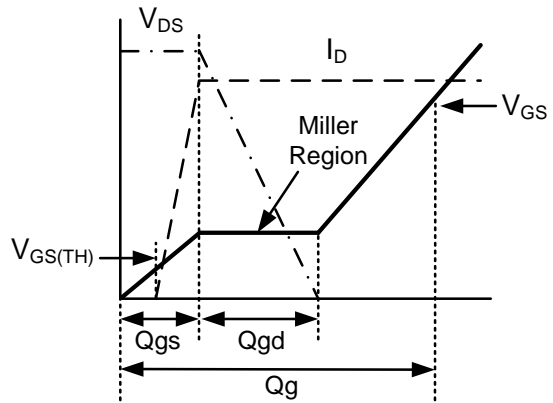
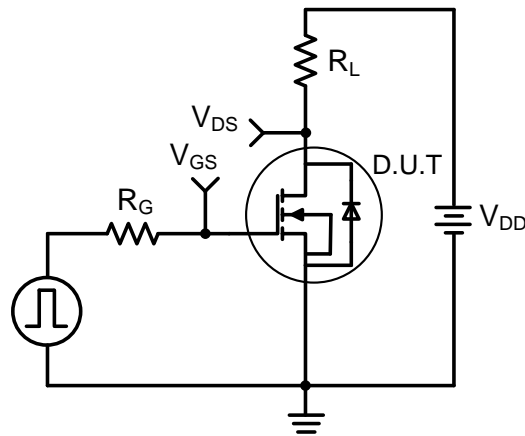
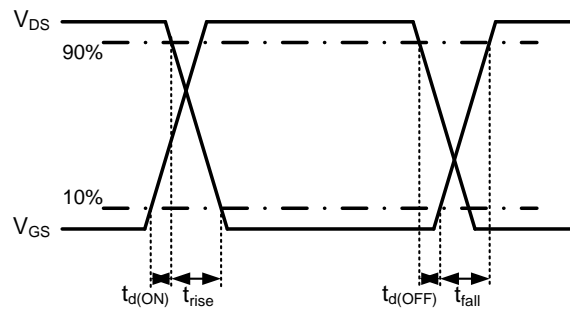


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuit

Figure 17. Gate Charge Test Circuit

Figure 18. Gate Charge Waveform

Figure 19. Resistive Switching Test Circuit

Figure 20. Resistive Switching Waveforms

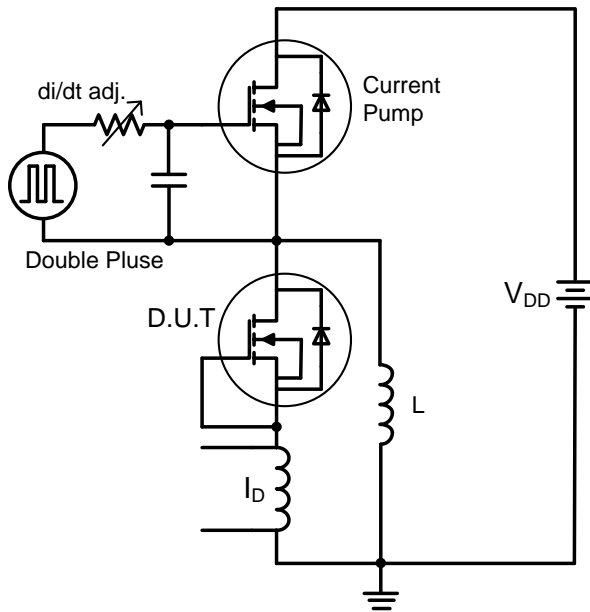


Figure 21. Diode Reverse Recovery Test Circuit

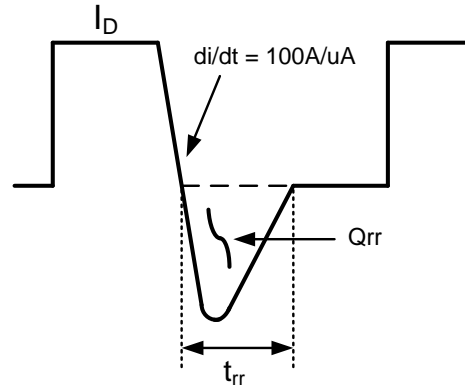


Figure 22. Diode Reverse Recovery Waveform

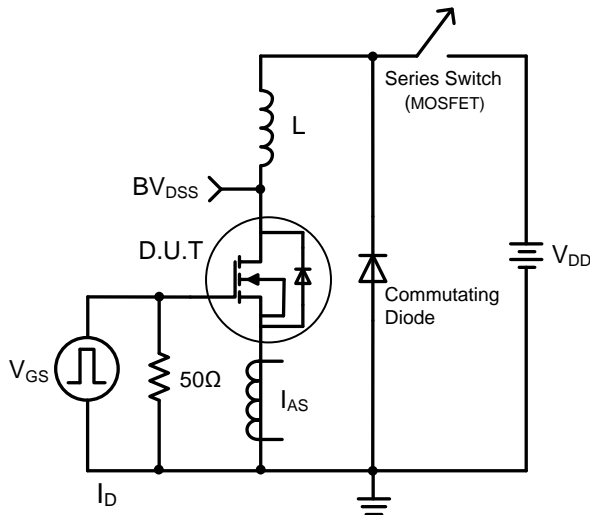


Figure 23. Unclamped Inductive Switching Test Circuit

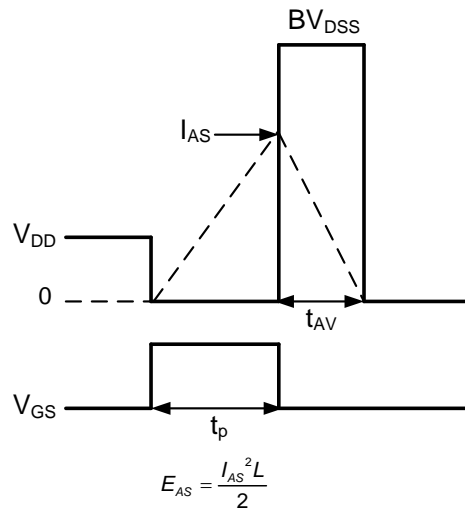


Figure 24. Unclamped Inductive Switching Waveforms



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